

MOSFET – Power, Single, N-Channel

40 V, 2.4 mΩ, 136 A

NTTFS002N04C

Features

- Small Footprint (3.3 x 3.3 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V_{DSS}	40	V
Gate-to-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current $R_{\theta JC}$ (Notes 1, 2, 3, 4)	Steady State	$T_C = 25^\circ\text{C}$	I_D	136
		$T_C = 100^\circ\text{C}$		77
Power Dissipation $R_{\theta JC}$ (Notes 1, 2, 3)		$T_C = 25^\circ\text{C}$	P_D	85
		$T_C = 100^\circ\text{C}$		27
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 3, 4)	Steady State	$T_A = 25^\circ\text{C}$	I_D	27
		$T_A = 100^\circ\text{C}$		19
Power Dissipation $R_{\theta JA}$ (Notes 1, 3)		$T_A = 25^\circ\text{C}$	P_D	3.2
		$T_A = 100^\circ\text{C}$		1.6
Pulsed Drain Current	$T_A = 25^\circ\text{C}$, $t_p = 10\ \mu\text{s}$	I_{DM}	676	A
Operating Junction and Storage Temperature Range		T_J , T_{Stg}	-55 to +175	°C
Source Current (Body Diode)		I_S	70.4	A
Single Pulse Drain-to-Source Avalanche Energy ($I_{L(pk)} = 10.2\ \text{A}$)		E_{AS}	268	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	°C

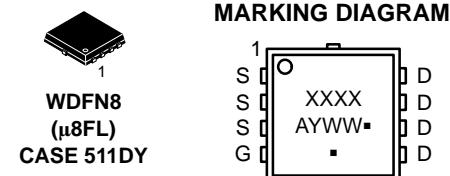
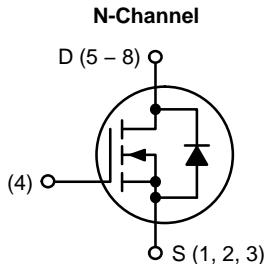
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS (Note 1)

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State (Note 3)	$R_{\theta JC}$	1.8	°C/W
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	46.5	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Psi (Ψ) is used as required per JESD51-12 for packages in which substantially less than 100% of the heat flows to single case surface.
3. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
4. Continuous DC current rating. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
40 V	2.4 mΩ @ 10 V	136 A



XXXX = Specific Device Code
 A = Assembly Location
 Y = Year
 WW = Work Week
 ■ = Pb-Free Package
 (Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

NTTFS002N04C

ELECTRICAL CHARACTERISTICS (T_J = 25 °C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	40			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 40 V	T _J = 25 °C		10	μA
			T _J = 125 °C		250	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = 20 V			100	nA
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 90 μA	2.5		3.5	V
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 50 A		2.0	2.4	mΩ
Forward Transconductance	g _{FS}	V _{DS} = 15 V, I _D = 50 A		92		S
CHARGES AND CAPACITANCES						
Input Capacitance	C _{iss}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 25 V		2250		pF
Output Capacitance	C _{oss}			1230		
Reverse Transfer Capacitance	C _{rss}			41		
Threshold Gate Charge	Q _{G(TH)}	V _{GS} = 10 V, V _{DS} = 20 V, I _D = 50 A		6.7		nC
Gate-to-Source Charge	Q _{GS}			11.4		
Gate-to-Drain Charge	Q _{GD}			5.7		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 10 V, V _{DS} = 20 V, I _D = 50 A		34		nC

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	t _{d(on)}	V _{GS} = 10 V, V _{DS} = 20 V, I _D = 50 A		11		ns
Rise Time	t _r			77		
Turn-Off Delay Time	t _{d(off)}			23		
Fall Time	t _f			7		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 50 A	T _J = 25 °C		0.84	1.2	V
			T _J = 125 °C		0.72		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 50 A			50		ns
Charge Time	t _a				25		
Discharge Time	t _b				25		
Reverse Recovery Charge	Q _{RR}				50		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

6. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

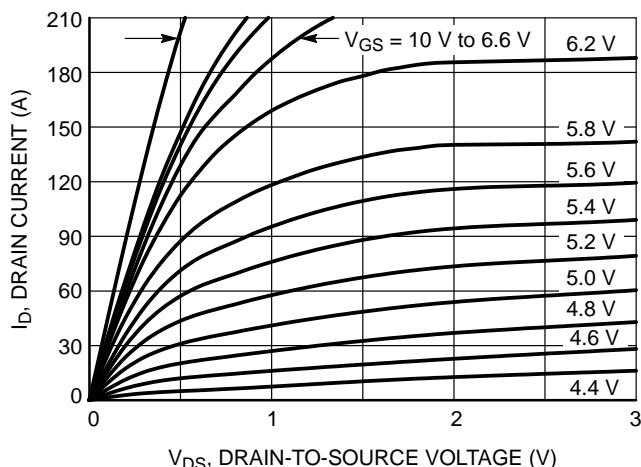


Figure 1. On-Region Characteristics

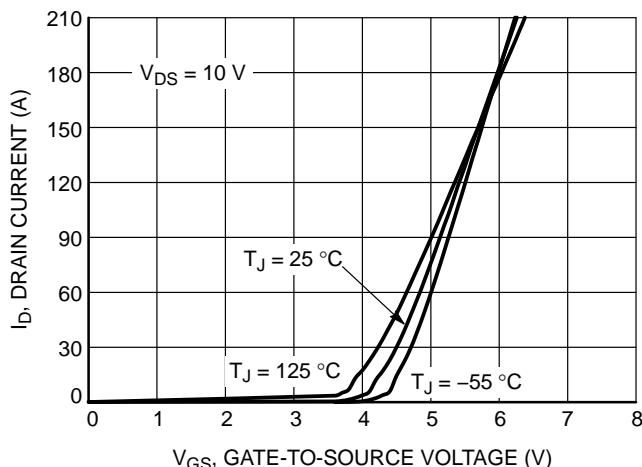


Figure 2. Transfer Characteristics

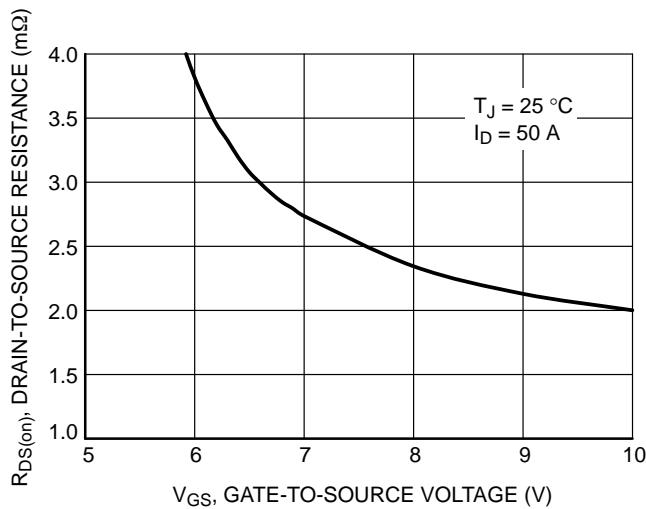


Figure 3. On-Resistance vs. Gate-to-Source Voltage

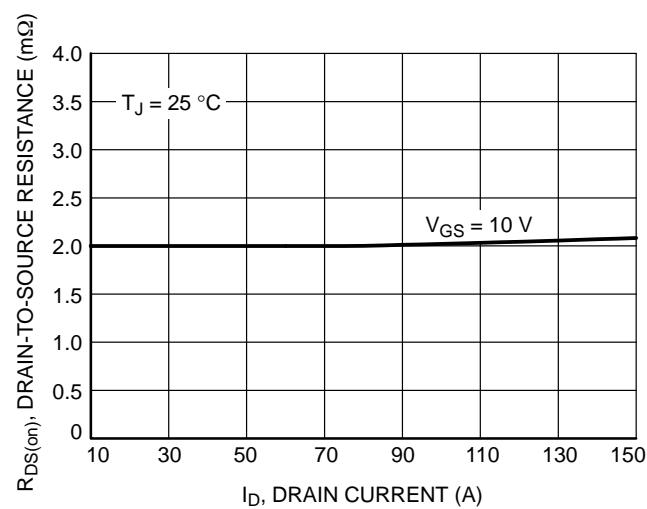


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

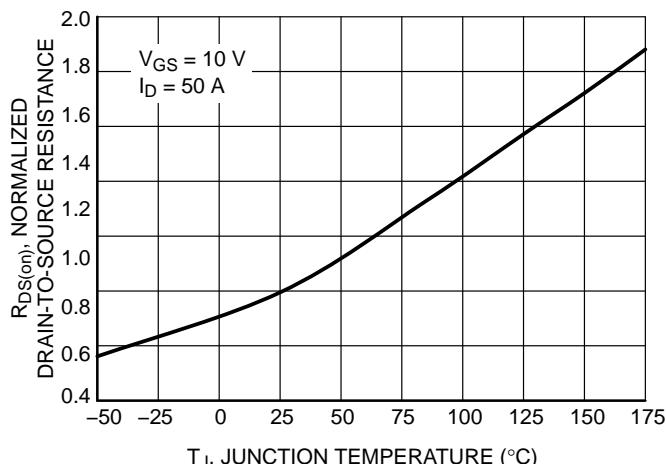


Figure 5. On-Resistance Variation with Temperature

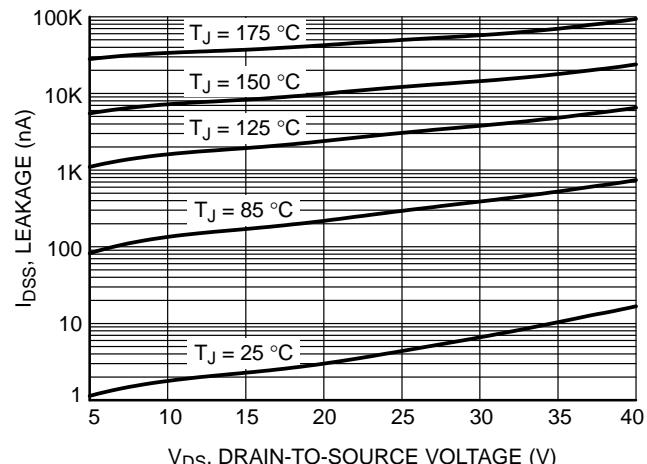


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

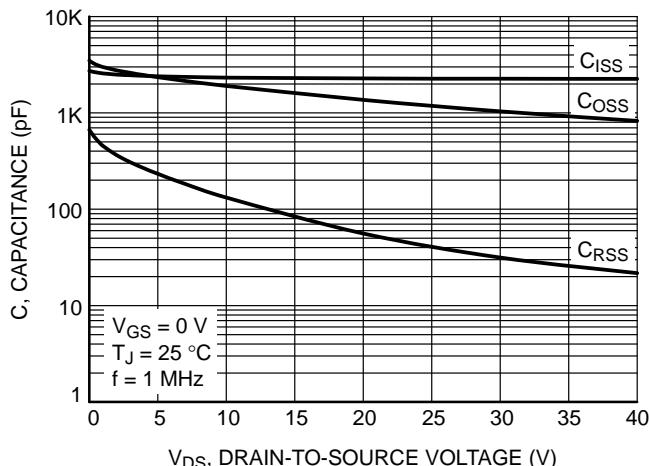


Figure 7. Capacitance Variation

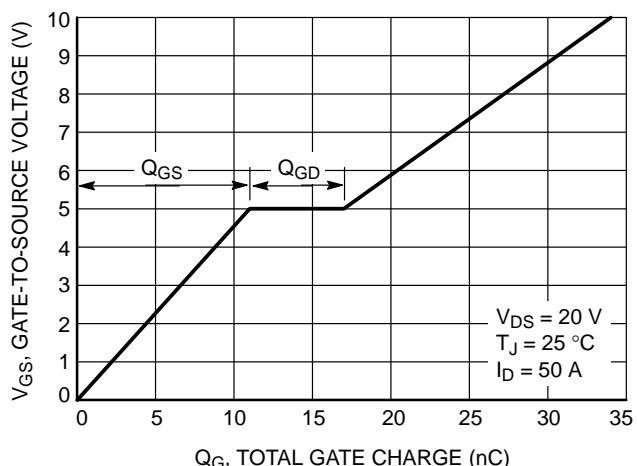


Figure 8. Gate-to-Source Voltage vs. Total Charge

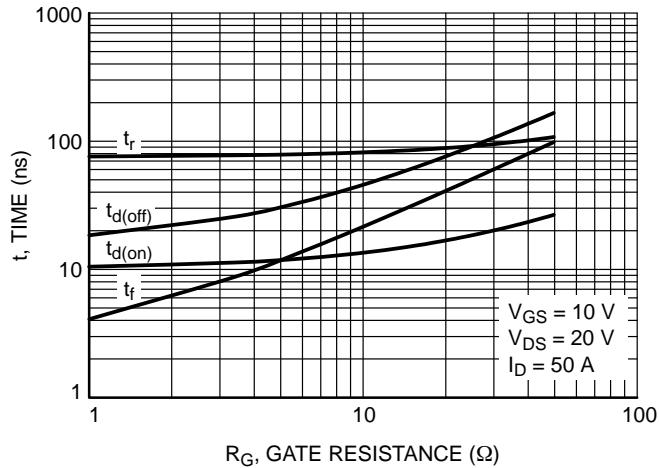


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

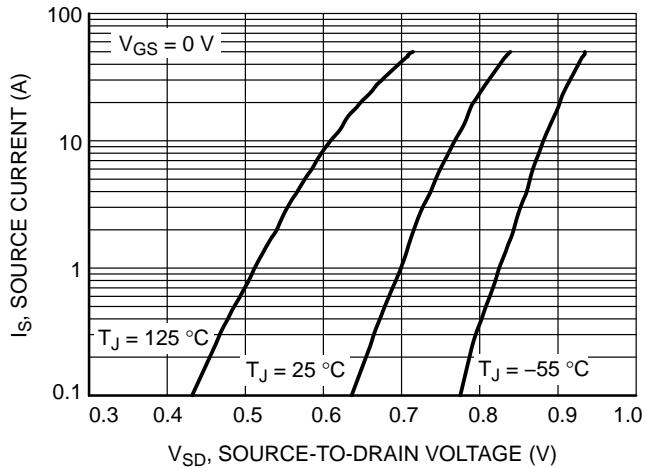


Figure 10. Diode Forward Voltage vs. Current

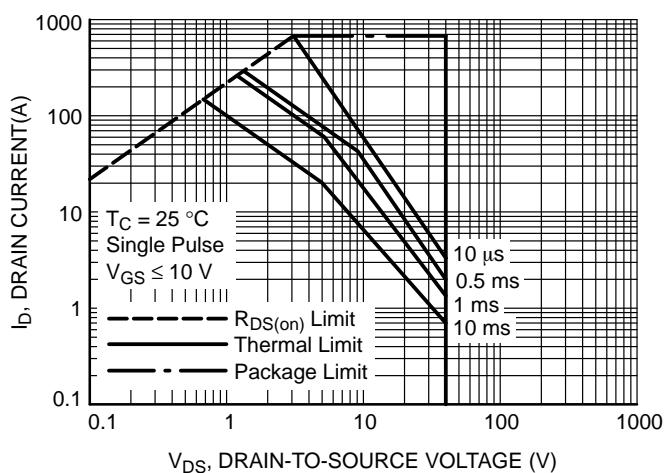


Figure 11. Maximum Rated Forward Biased Safe Operating Area

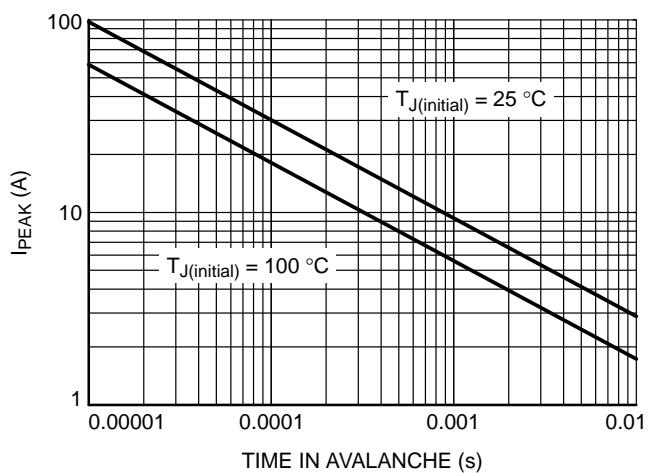


Figure 12. I_{PEAK} vs. Time in Avalanche

NTTFS002N04C

TYPICAL CHARACTERISTICS

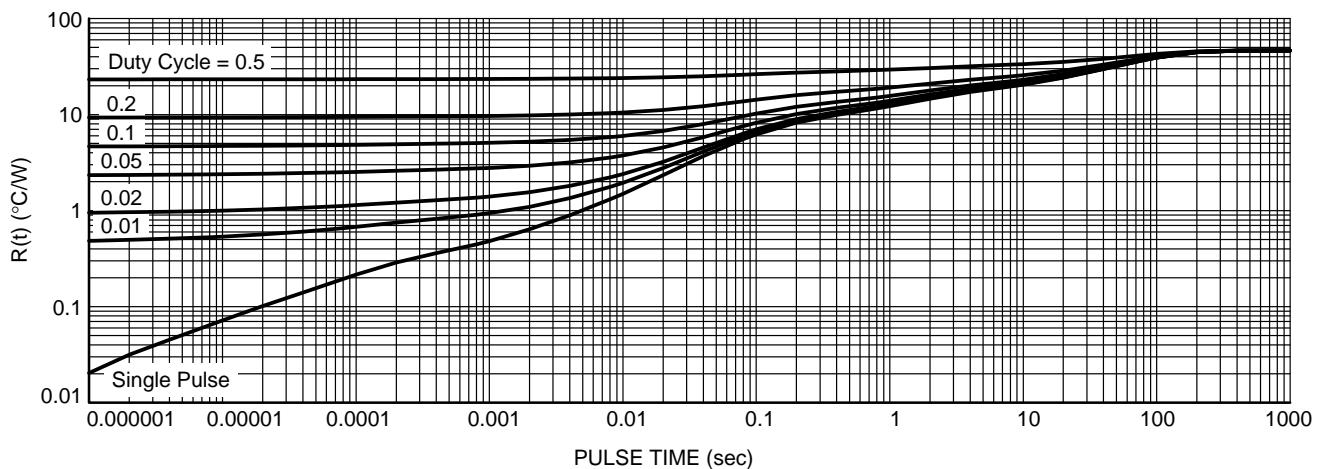


Figure 13. Thermal Characteristics

DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NTTFS002N04CTAG	02NC	WDFN8 (Pb-Free)	1500 / Tape & Reel

[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

NTTFS002N04C

REVISION HISTORY

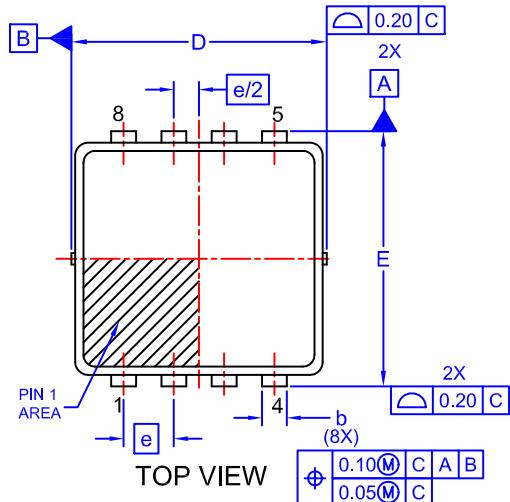
Revision	Description of Changes	Date
0	Initial Production Data Sheet release.	6/19/2019
1	Rebranded the Data Sheet to onsemi format.	10/21/2025

WDFN8 3.3x3.3, 0.65P

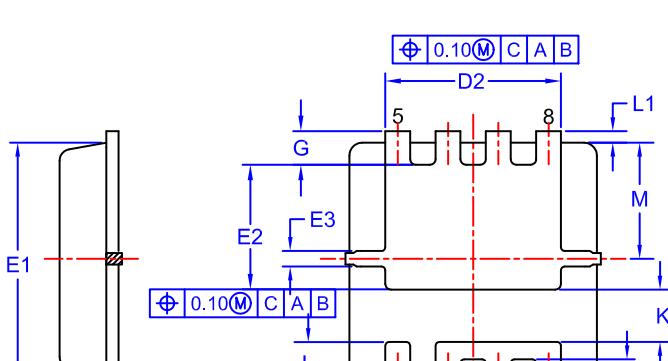
CASE 511DY

ISSUE A

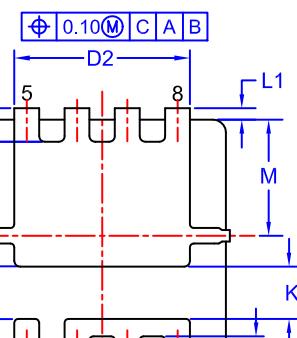
DATE 21 AUG 2018



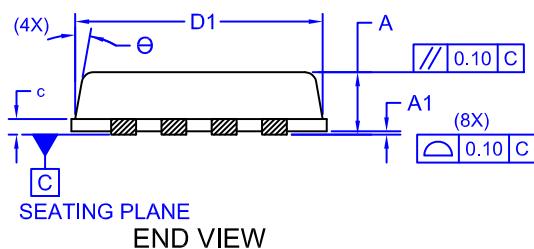
TOP VIEW



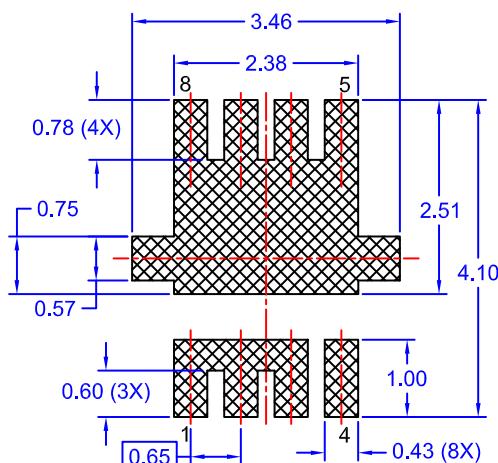
SIDE VIEW



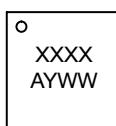
BOTTOM VIEW



END VIEW



RECOMMENDED LAND PATTERN

GENERIC
MARKING DIAGRAM*

XXXX = Specific Device Code

A = Assembly Location

Y = Year Code

WW = Work Week Code

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	0.00	-	0.05
b	0.23	0.33	0.43
c	0.15	0.20	0.25
D	3.20	3.30	3.40
D1	2.95	3.13	3.30
D2	1.98	2.20	2.40
E	3.20	3.30	3.40
E1	2.80	3.00	3.15
E2	1.40	1.60	1.80
E3	0.15	0.25	0.40
e	0.65 BSC		
G	0.30	0.43	0.55
G1	0.25	0.35	0.45
K	0.55	0.75	0.95
L	0.35	0.52	0.65
L1	0.06	0.15	0.30
M	1.35	1.50	1.60
Θ	0	-	12

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	WDFN8 3.3x3.3, 0.65P	PAGE 1 OF 1

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